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In the Claims:

1. (currently amended) A method for increasing the manufacturing yield for a predetermined device, said device composed of one or more multiple layer die, said method comprising the steps of:

determining diagnostically the number of functioning layers of each of said multiple layer die; and

sorting each of said multiple layer die based on said number of functioning layers,  
wherein said at least one of said multiple layer die comprises a first selectively bonded semiconductor layer vertically supported on a substrate, said bonded semiconductor layer containing weak bond regions and strong bond regions;  
a second selectively bonded semiconductor layer vertically supported on said first selectively bonded semiconductor layer;  
wherein a semiconductor device portion is created at or on said weak bond regions.  
wherein said semiconductor device portion vertically spans said first selectively bonded semiconductor layer and said second selectively bonded semiconductor layer; and  
wherein said die is formed by dicing said bonded semiconductor layers.

2. (original) The method of claim 1, further comprising combining two or more of said multiple layer die so that functioning layers of each of said multiple layer die are interconnected with each other.

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3. (original) The method of claim 1, wherein said determining step is performed through testing of one or more edge interconnects of said multiple layer die.

4. (original) The method of claim 2, wherein said combining step comprises vertical stacking of two or more die.

5. (original) The method of claim 2 wherein said combining step comprises edge stacking of two or more die.

6. (original) The method of claim 1, further comprising storing health data associated with each said multiple layer die on one or more layers or a portion of one or more layers .

7. (original) The method of claim 6, wherein said health data comprises indication of known good layers or known bad layers on each said multiple layer die.

8. (canceled)

9. (currently amended) A method for providing a device having at least a predetermined number of known good layers, said device composed of one or more multiple layer die, said method comprising the steps of:

determining diagnostically the number of functioning layers of each of said multiple layer die;

sorting each of said multiple layer die based on said number of functioning layers into a plurality of bins, each bin having an associated minimum number of known good layers; and

selecting one of said multiple layer die having said predetermined number of known good layers from one of said bins having an associated minimum number of known good layers at least equal to said predetermined number of known good layers, wherein said at least one of said multiple layer die comprises

first selectively bonded semiconductor layer vertically supported on a substrate,  
said bonded semiconductor layer containing weak bond regions and strong bond regions;

a second selectively bonded semiconductor layer vertically supported on said first selectively bonded semiconductor layer;

wherein a semiconductor device portion is created at or on said weak bond regions,

wherein said semiconductor device portion vertically spans said first selectively bonded semiconductor layer and said second selectively bonded semiconductor layer, and  
wherein said die is formed by dicing said bonded semiconductor layers..

11. (original) A method for providing a device having at least a predetermined number of known good layers, said device composed of one or more multiple layer die, said method comprising the steps of:

determining diagnostically the number of functioning layers of each of said multiple layer die;

sorting each of said multiple layer die based on said number of functioning layers into a plurality of bins, each bin having an associated minimum number of known good layers;

selecting a plurality of said multiple layer die having a sum of known good layers at least equal to said predetermined number of known good layers; and

combining said selected plurality of multiple layer die to form a combined die having a number of known good layers at least equal to said predetermined number of known good layers.

12. (original) The method as in claim 11, wherein said selected plurality of multiple layer die are combined horizontally and interconnected through one or more edge interconnects on each of said selected plurality of multiple layer die.

13. (original) The method as in claim 11, wherein said selected plurality of multiple layer die are combined vertically.

14. (original) The method of claim 11, wherein said at least one of said multiple layer die comprises

a first selectively bonded semiconductor layer vertically supported on a substrate, said bonded semiconductor layer containing weak bond regions and strong bond regions;

sorting said second multiple layer die portion into one of said bins having a minimum number of known good layers corresponding to the number of known good layers of said second multiple layer die portion.

16. (original) The method of claim 15, wherein said slicing occurs at a known bad layer of said selected multiple layer die.

17. (original) The method of claim 15, wherein said at least one of said multiple layer die comprises

a first selectively bonded semiconductor layer vertically supported on a substrate, said bonded semiconductor layer containing weak bond regions and strong bond regions; a second selectively bonded semiconductor layer vertically supported on said first selectively bonded semiconductor layer;

wherein a semiconductor device portion is created at or on said weak bond regions,

wherein said semiconductor device portion vertically spans said first selectively bonded semiconductor layer and said second selectively bonded semiconductor layer; and wherein said die is formed by dicing said bonded semiconductor layers.

a second selectively bonded semiconductor layer vertically supported on said first selectively bonded semiconductor layer;

wherein a semiconductor device portion is created at or on said weak bond regions,

wherein said semiconductor device portion vertically spans said first selectively bonded semiconductor layer and said second selectively bonded semiconductor layer; and

wherein said die is formed by dicing said bonded semiconductor layers.

15. (original) A method for providing a device having at least a predetermined number of known good layers, said device composed of one or more multiple layer die, said method comprising the steps of:

determining diagnostically the number of functioning layers of each of said multiple layer die;

sorting each of said multiple layer die based on said number of functioning layers into a plurality of bins, each bin having an associated minimum number of known good layers;

selecting one of said a multiple layer die a number of known good layers greater than said predetermined number of known good layers;

slicing said selected multiple layer die to form a first multiple layer die portion having a number of known good layers at least equal to said predetermined number of known good layers and a second multiple layer die portion; and